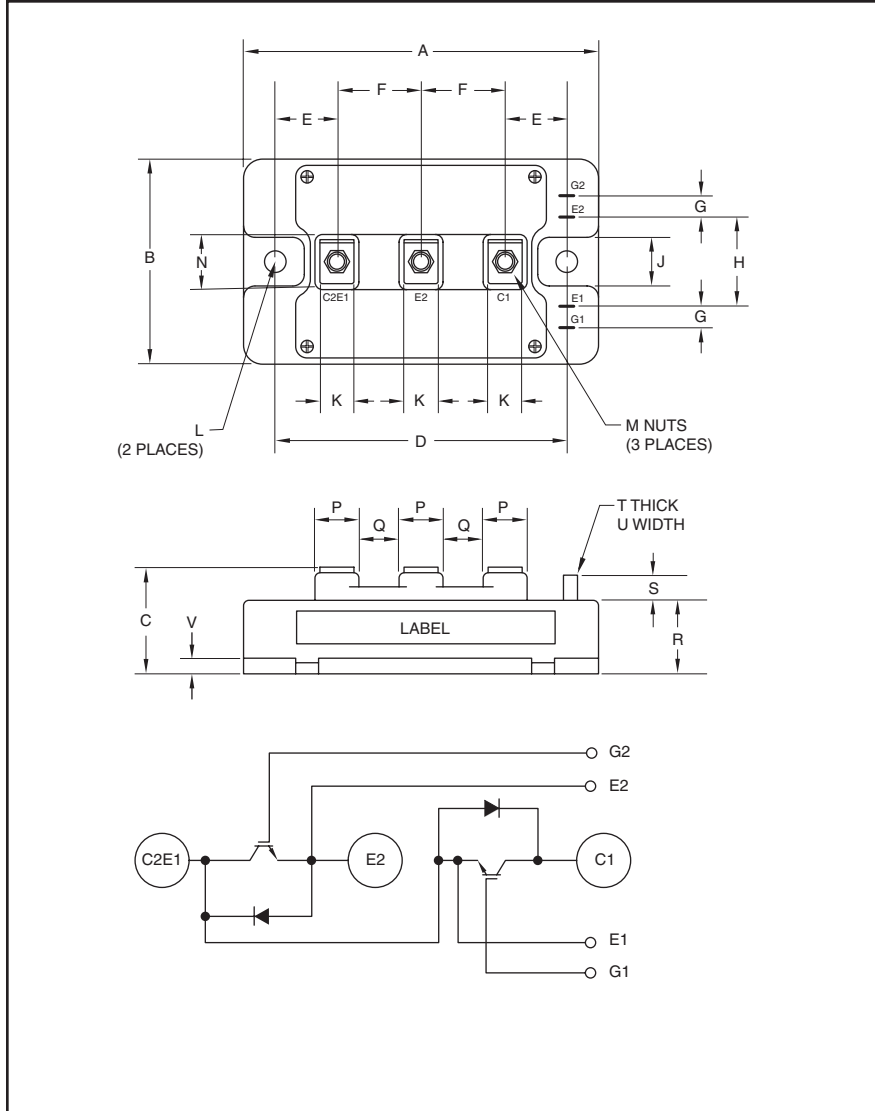


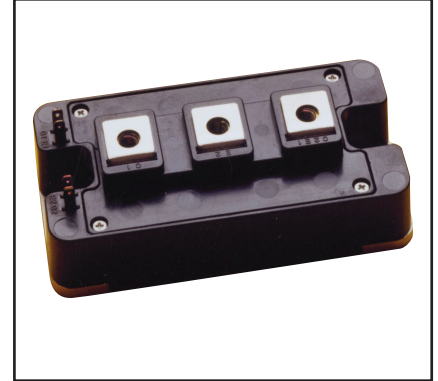
### Dual IGBTMOD™ A-Series Module 200 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	3.70	94.0
B	1.89	48.0
C	1.14+0.004/-0.02	29.0+0.1/-0.5
D	3.15±0.01	80.0±0.25
E	0.67	17.0
F	0.91	23.0
G	0.16	4.0
H	0.71	18.0
J	0.51	13.0
K	0.47	12.0

Dimensions	Inches	Millimeters
L	0.26 Dia.	Dia. 6.5
M	M5 Metric	M5
N	0.79	20.0
P	0.63	16.0
Q	0.28	7.0
R	0.83	21.2
S	0.30	7.5
T	0.02	0.5
U	0.110	2.8
V	0.16	4.0



#### Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of two IGBT Transistors in a half-bridge configuration with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

#### Features:

- Low Drive Power
- Low  $V_{CE(sat)}$
- Discrete Super-Fast Recovery Free-Wheel Diode
- Isolated Baseplate for Easy Heat Sinking

#### Applications:

- AC Motor Control
- UPS
- Battery Powered Supplies

#### Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM200DY-24A is a 1200V ( $V_{CES}$ ), 200 Ampere Dual IGBTMOD™ Power Module.

Type	Current Rating Amperes	$V_{CES}$ Volts (x 50)
CM	200	24



Powerex, Inc., 173 Pavilion Lane, Youngwood, Pennsylvania 15697 (724) 925-7272

**CM200DY-24A**  
**Dual IGBTMOD™ A-Series Module**  
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**Absolute Maximum Ratings,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Ratings	Symbol	CM200DY-24A	Units
Junction Temperature	$T_j$	-40 to 150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-40 to 125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E Short)	$V_{CES}$	1200	Volts
Gate-Emitter Voltage (C-E Short)	$V_{GES}$	$\pm 20$	Volts
Collector Current (DC, $T_C = 86^\circ\text{C}^*$ )	$I_C$	200	Amperes
Peak Collector Current	$I_{CM}$	400**	Amperes
Emitter Current*** ( $T_C = 25^\circ\text{C}$ )	$I_E$	200	Amperes
Peak Emitter Current***	$I_{EM}$	400**	Amperes
Maximum Collector Dissipation ( $T_C = 25^\circ\text{C}^*$ , $T_j \leq 150^\circ\text{C}$ )	$P_C$	1340	Watts
Mounting Torque, M5 Main Terminal	—	30	in-lb
Mounting Torque, M6 Mounting	—	40	in-lb
Weight	—	310	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	$V_{ISO}$	2500	Volts

**Static Electrical Characteristics,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$	—	—	1.0	mA
Gate Leakage Current $I_{GES}$	$V_{GE} = V_{GES}$ , $V_{CE} = 0V$	—	—	0.5	—	$\mu\text{A}$
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 20\text{mA}$ , $V_{CE} = 10V$	6.0	7.0	8.0	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 200A$ , $V_{GE} = 15V$ , $T_j = 25^\circ\text{C}$	—	2.1	3.0	Volts
		$I_C = 200A$ , $V_{GE} = 15V$ , $T_j = 125^\circ\text{C}$	—	2.4	—	Volts
Total Gate Charge	$Q_G$	$V_{CC} = 600V$ , $I_C = 200A$ , $V_{GE} = 15V$	—	1000	—	nC
Emitter-Collector Voltage**	$V_{EC}$	$I_E = 200A$ , $V_{GE} = 0V$	—	—	3.8	Volts

**Dynamic Electrical Characteristics,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	$C_{ies}$		—	—	35	nf
Output Capacitance	$C_{oes}$	$V_{CE} = 10V$ , $V_{GE} = 0V$	—	—	3	nf
Reverse Transfer Capacitance	$C_{res}$		—	—	0.68	nf
Inductive	Turn-on Delay Time	$V_{CC} = 600V$ , $I_C = 200A$ , $V_{GE1} = V_{GE2} = 15V$ , $R_G = 1.6\Omega$ ,	—	—	130	ns
	Load					
Switch	Turn-off Delay Time	Inductive Load	—	—	450	ns
	Time					
Diode Reverse Recovery Time***	$t_{rr}$	Switching Operation,	—	—	150	ns
Diode Reverse Recovery Charge***	$Q_{rr}$	$I_E = 200A$	—	9.0	—	$\mu\text{C}$

\* $T_C$ ,  $T_f$  measured point is just under the chips.

\*\*Pulse width and repetition rate should be such that device junction temperature ( $T_j$ ) does not exceed  $T_{j(max)}$  rating.

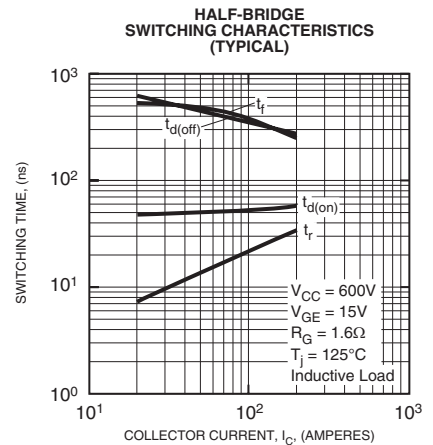
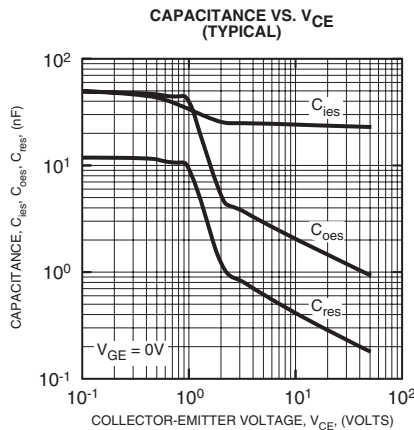
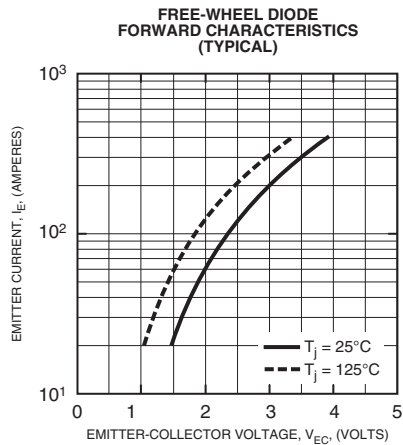
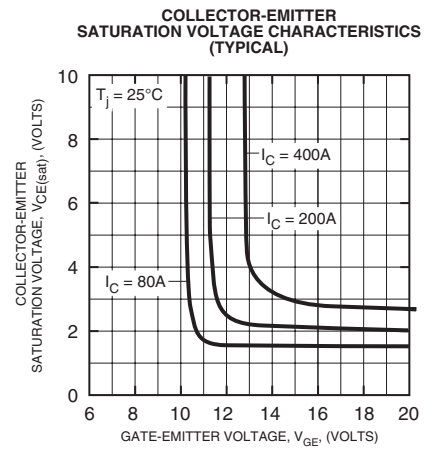
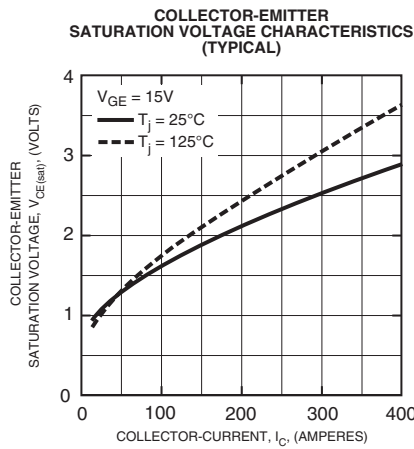
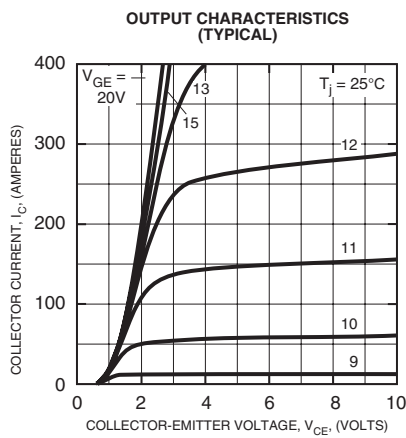
\*\*\*Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDI).

**CM200DY-24A**  
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**Thermal and Mechanical Characteristics,  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case*	$R_{th(j-c)Q}$	Per IGBT 1/2 Module	—	—	0.093	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case*	$R_{th(j-c)D}$	Per FWDi 1/2 Module	—	—	0.17	$^\circ\text{C/W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per 1/2 Module, Thermal Grease Applied	—	0.022	—	$^\circ\text{C/W}$
External Gate Resistance	$R_G$		1.6	—	21	$\Omega$

\* $T_C$ ,  $T_f$  measured point is just under the chips.



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